

WEST[Generate Collection](#)[Print](#)**Search Results - Record(s) 1 through 6 of 6 returned.**☐ 1. Document ID: US 6383942 B1

L4: Entry 1 of 6

File: USPT

May 7, 2002

US-PAT-NO: 6383942

DOCUMENT-IDENTIFIER: US 6383942 B1

TITLE: Dry etching method

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
Draw Desc	Image								

KVMC

☐ 2. Document ID: US 5963812 A

L4: Entry 2 of 6

File: USPT

Oct 5, 1999

US-PAT-NO: 5963812

DOCUMENT-IDENTIFIER: US 5963812 A

TITLE: Manufacturing method of a semiconductor apparatus having an electron donative surface in a side wall portion

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
Draw Desc	Image								

KVMC

☐ 3. Document ID: US 5580808 A

L4: Entry 3 of 6

File: USPT

Dec 3, 1996

US-PAT-NO: 5580808

DOCUMENT-IDENTIFIER: US 5580808 A

TITLE: Method of manufacturing a ROM device having contact holes treated with hydrogen atoms and energy beam

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
Draw Desc	Image								

KVMC

☐ 4. Document ID: US 5569614 A

L4: Entry 4 of 6

File: USPT

Oct 29, 1996

US-PAT-NO: 5569614

DOCUMENT-IDENTIFIER: US 5569614 A

TITLE: Method of forming metal pattern including a schottky diode

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	KWIC
Draw Desc	Image									

5. Document ID US 5527730 A

L4: Entry 5 of 6

File: USPT

Jun 18, 1996

US-PAT-NO: 5527730

DOCUMENT-IDENTIFIER: US 5527730 A

TITLE: Method of forming a capacitor having contact hole treated with hydrogen atoms and energy beam

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	KWIC
Draw Desc	Image									

6. Document ID: US 5393565 A

L4: Entry 6 of 6

File: USPT

Feb 28, 1995

US-PAT-NO: 5393565

DOCUMENT-IDENTIFIER: US 5393565 A

TITLE: Method for deposition of a refractory metal nitride and method for formation of a conductive film containing a refractory metal nitride

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	KWIC
Draw Desc	Image									

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L1 and (reactive adj gases)

6

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L9: Entry 1 of 27

File: USPT

Dec 31, 2002

US-PAT-NO: 6500742

DOCUMENT-IDENTIFIER: US 6500742 B1

TITLE: Construction of a film on a semiconductor wafer ✓

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
Draw Desc	Image								

KIMC

☐ 2. Document ID: US 6495458 B2

L9: Entry 2 of 27

File: USPT

Dec 17, 2002

US-PAT-NO: 6495458

DOCUMENT-IDENTIFIER: US 6495458 B2

TITLE: Method for producing low carbon/oxygen conductive layers

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
Draw Desc	Image								

KIMC

☐ 3. Document ID: US 6491978 B1

L9: Entry 3 of 27

File: USPT

Dec 10, 2002

US-PAT-NO: 6491978

DOCUMENT-IDENTIFIER: US 6491978 B1

TITLE: Deposition of CVD layers for copper metallization using novel metal organic chemical vapor deposition (MOCVD) precursors ✓

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
Draw Desc	Image								

KIMC

☐ 4. Document ID: US 6465345 B1

L9: Entry 4 of 27

File: USPT

Oct 15, 2002

US-PAT-NO: 6465345

DOCUMENT-IDENTIFIER: US 6465345 B1

TITLE: Prevention of inter-channel current leakage in
semiconductors

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
Draw Desc	Image								

KMC

☐ 5. Document ID: US 6451692 B1

L9: Entry 5 of 27

File: USPT

Sep 17, 2002

US-PAT-NO: 6451692

DOCUMENT-IDENTIFIER: US 6451692 B1

TITLE: Preheating of chemical vapor deposition precursors

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
Draw Desc	Image								

KMC

☐ 6. Document ID: US 6448187 B2

L9: Entry 6 of 27

File: USPT

Sep 10, 2002

US-PAT-NO: 6448187

DOCUMENT-IDENTIFIER: US 6448187 B2

TITLE: Method of improving moisture resistance of low dielectric
constant films

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
Draw Desc	Image								

KMC

☐ 7. Document ID: US 6444542 B2

L9: Entry 7 of 27

File: USPT

Sep 3, 2002

US-PAT-NO: 6444542

DOCUMENT-IDENTIFIER: US 6444542 B2

TITLE: Integrated circuit and method

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
Draw Desc	Image								

KMC

☐ 8. Document ID: US 6444036 B2

L9: Entry 8 of 27

File: USPT

Sep 3, 2002

US-PAT-NO: 6444036

DOCUMENT-IDENTIFIER: US 6444036 B2

TITLE: Construction of a film on a semiconductor wafer

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	KWIC
Draw Desc	Image									

☐ 9. Document ID: US 6403414 B2

L9: Entry 9 of 27

File: USPT

Jun 11, 2002

US-PAT-NO: 6403414

DOCUMENT-IDENTIFIER: US 6403414 B2

TITLE: Method for producing low carbon/oxygen conductive layers

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	KWIC
Draw Desc	Image									

☐ 10. Document ID: US 6351039 B1

L9: Entry 10 of 27

File: USPT

Feb 26, 2002

US-PAT-NO: 6351039

DOCUMENT-IDENTIFIER: US 6351039 B1

TITLE: Integrated circuit dielectric and method

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	KWIC
Draw Desc	Image									

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L7 and tungsten

27



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L7 and tungsten	27

Database: **US Patents Full-Text Database** 
US Pre-Grant Publication Full-Text Database
JPO Abstracts Database
EPO Abstracts Database
Derwent World Patents Index
IBM Technical Disclosure Bulletins 

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4/855,609

Set Name Query

side by side

DB=USPT; PLUR=YES; OP=ADJ

<u>L9</u>	L7 and tungsten
<u>L8</u>	L7 and 438/\$.class
<u>L7</u>	L5 and silane
<u>L6</u>	L5 and (stacked near barrier)
<u>L5</u>	(Barrier adj layer) and (adhesion adj layer) and (copper) and ((reactive adj gases) or TDMAT or TDEAT or TiCl4)
<u>L4</u>	L1 and (reactive adj gases)
<u>L3</u>	L1 and (adhesion near layer)
<u>L2</u>	L1 near7 adhesion
<u>L1</u>	stacked near2 barrier

Hit Count Set Name

result set

27	<u>L9</u>
0	<u>L8</u>
29	<u>L7</u>
0	<u>L6</u>
68	<u>L5</u>
6	<u>L4</u>
3	<u>L3</u>
0	<u>L2</u>
220	<u>L1</u>

END OF SEARCH HISTORY

WEST[Generate Collection](#)[Print](#)**Search Results - Record(s) 1 through 3 of 3 returned.**☐ 1. Document ID: US 6447826 B1

L3: Entry 1 of 3

File: USPT

Sep 10, 2002

US-PAT-NO: 6447826

DOCUMENT-IDENTIFIER: US 6447826 B1

TITLE: Packaging for meat and foodstuff

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KWIC
Draw Desc	Image										

☐ 2. Document ID: US 6284595 B1

L3: Entry 2 of 3

File: USPT

Sep 4, 2001

US-PAT-NO: 6284595

DOCUMENT-IDENTIFIER: US 6284595 B1

TITLE: Method for fabricating stacked capacitor having excellent anti-oxidation property

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KWIC
Draw Desc	Image										

☐ 3. Document ID: US 6228701 B1

L3: Entry 3 of 3

File: USPT

May 8, 2001

US-PAT-NO: 6228701

DOCUMENT-IDENTIFIER: US 6228701 B1

TITLE: Apparatus and method for minimizing diffusion in stacked capacitors formed on silicon plugs

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	KWIC
Draw Desc	Image									

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Terms	Documents
L1 and (adhesion near layer)	3

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